

FIG. 1

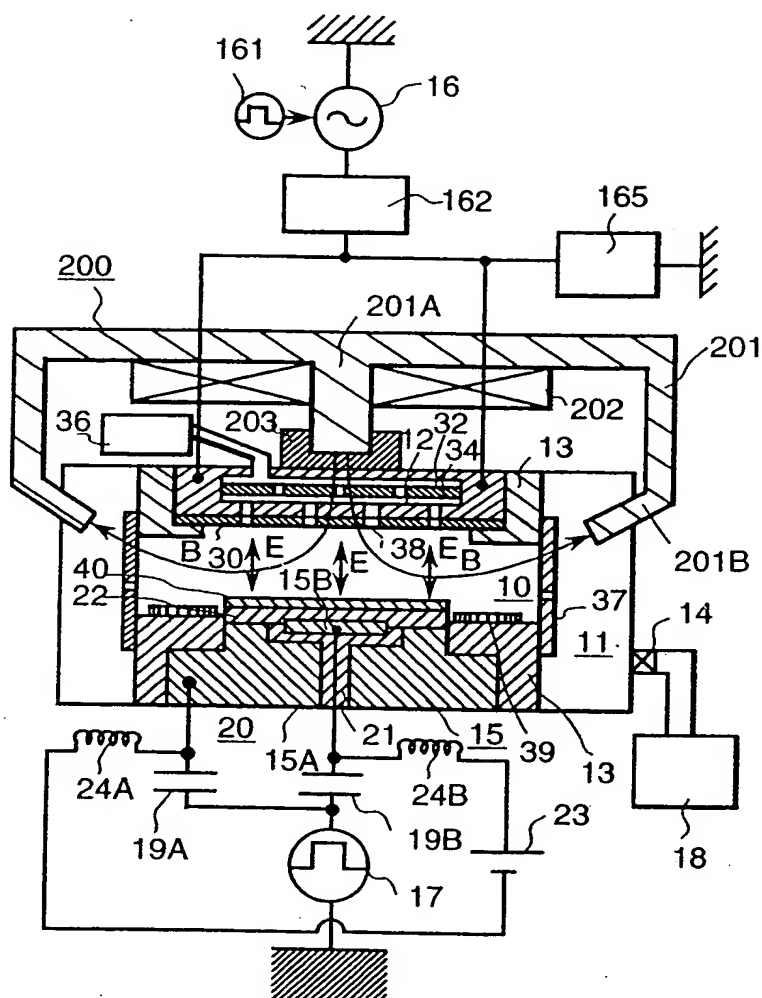


FIG. 2

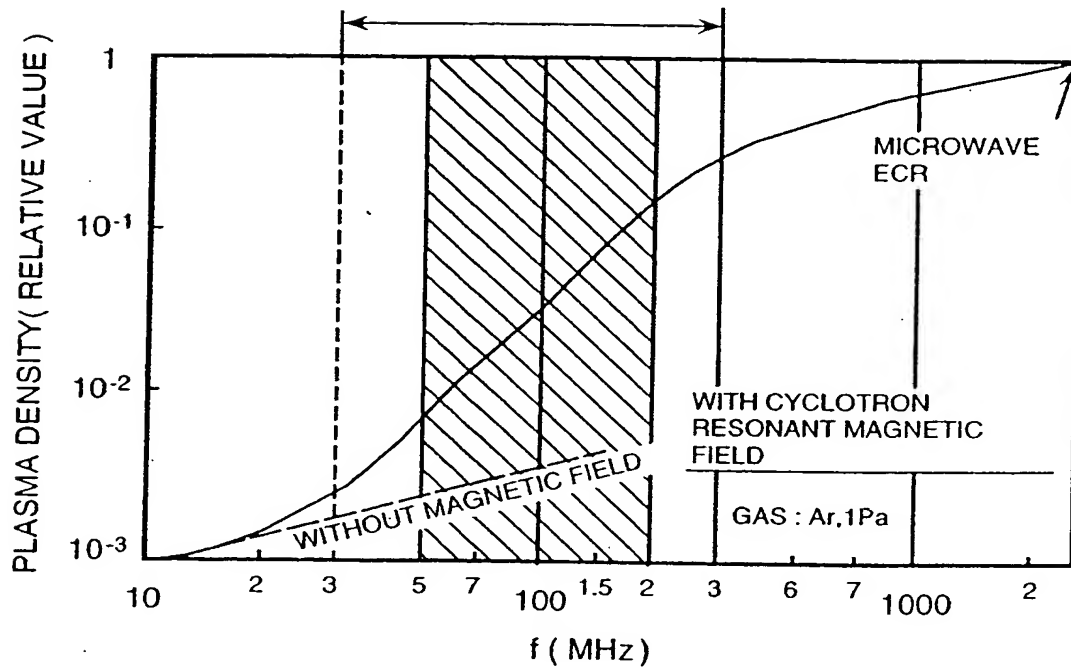
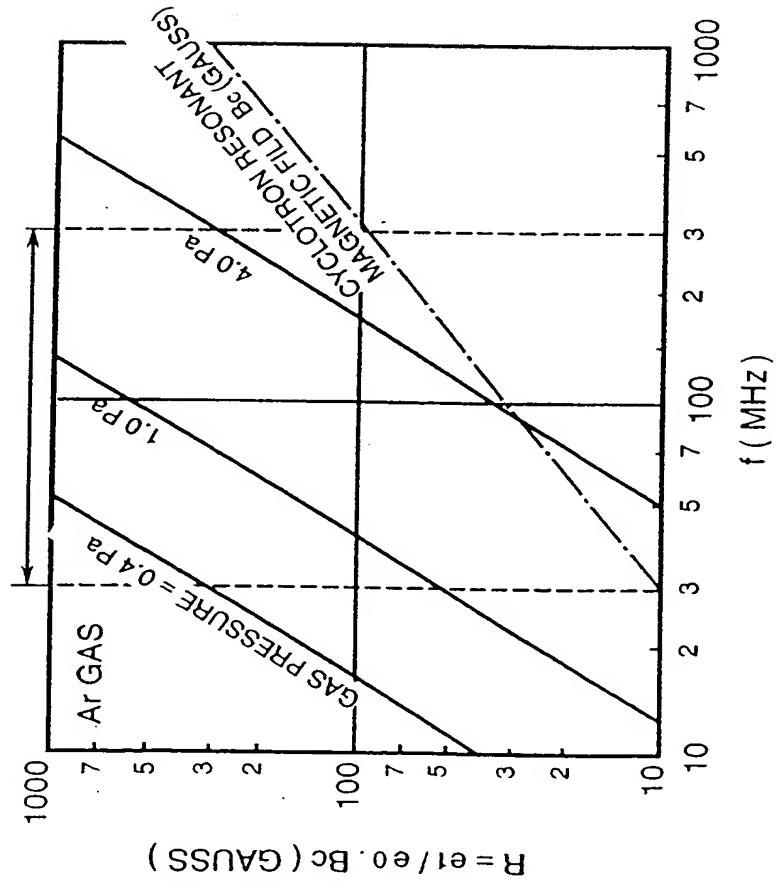


FIG. 3



$$B_c = 2\pi f \cdot \frac{m}{e}$$

$e_0$  : ENERGY OBTAINED BY ELECTRON DURING ONE CYCLE OF RF UNDER CONDITION WITHOUT MAGNETIC FIELD

$e_1$  : ENERGY OBTAINED BY ELECTRON DURING ONE CYCLE OF RF UNDER CONDITION APPLIED WITH CYCLOTRON RESONANT MAGNETIC FIELD

FIG. 4

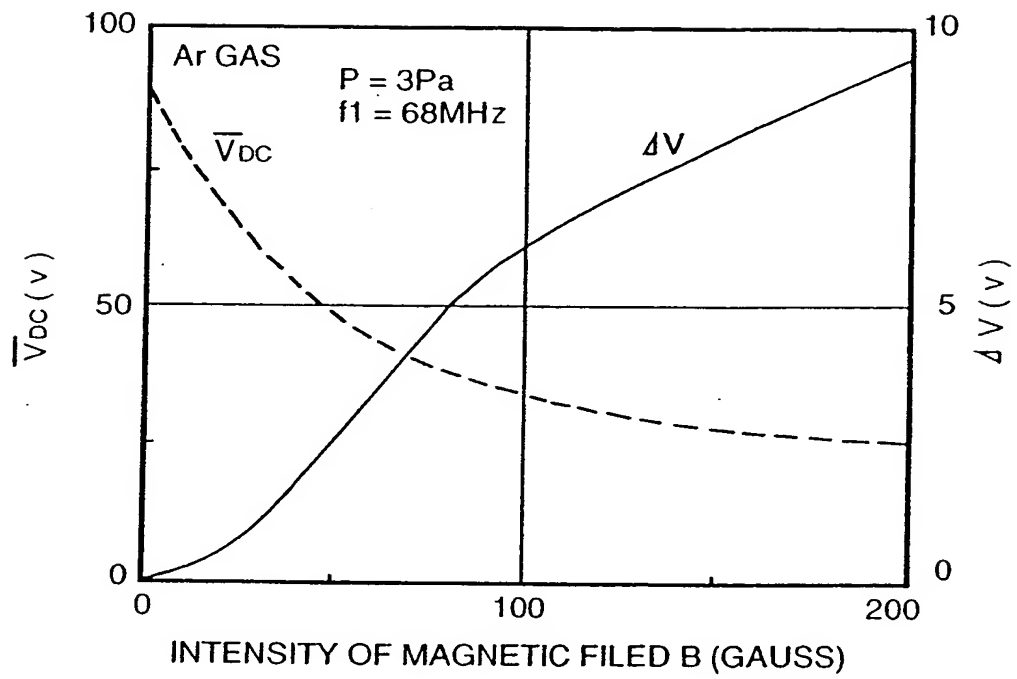


FIG. 5

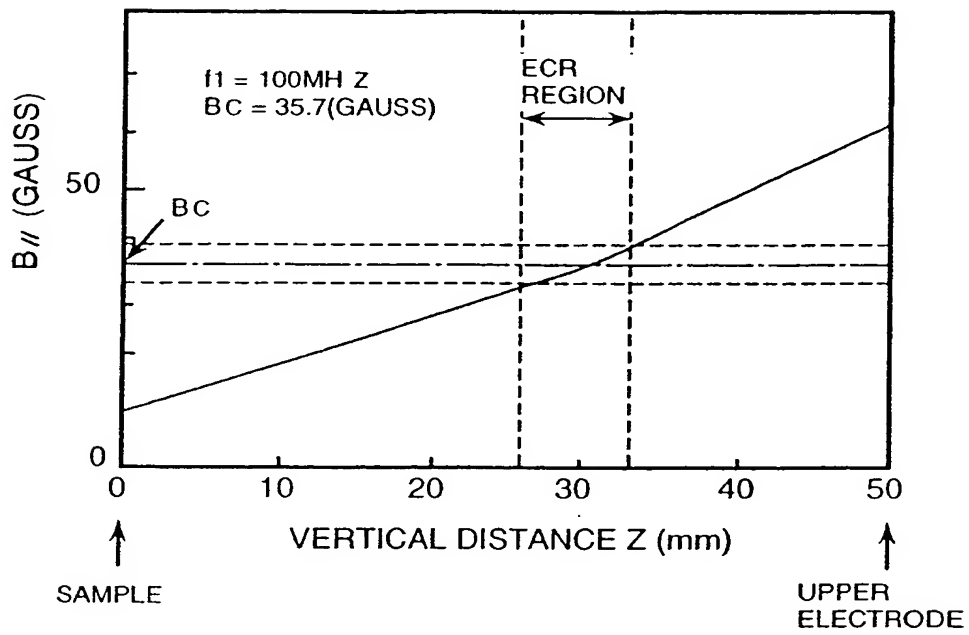


FIG. 6

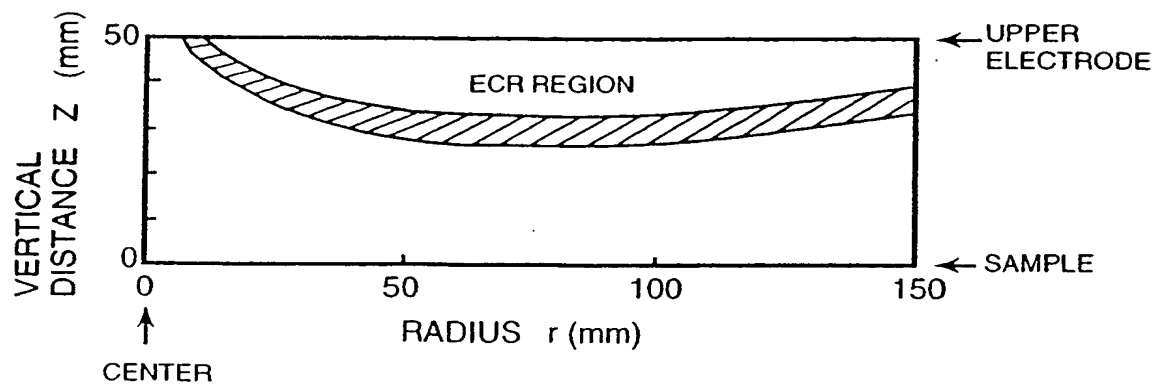


FIG.7(A)

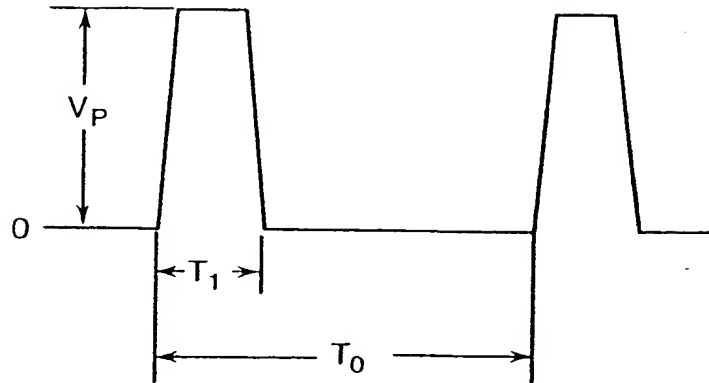
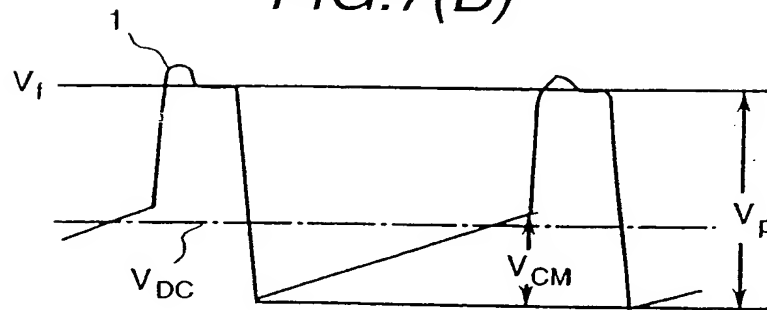


FIG.7(B)



$$V_{CM} = \frac{q}{c} = \frac{i_i \cdot (T_0 - T_1)}{(\epsilon_\gamma \epsilon_0 / d) \times K}$$

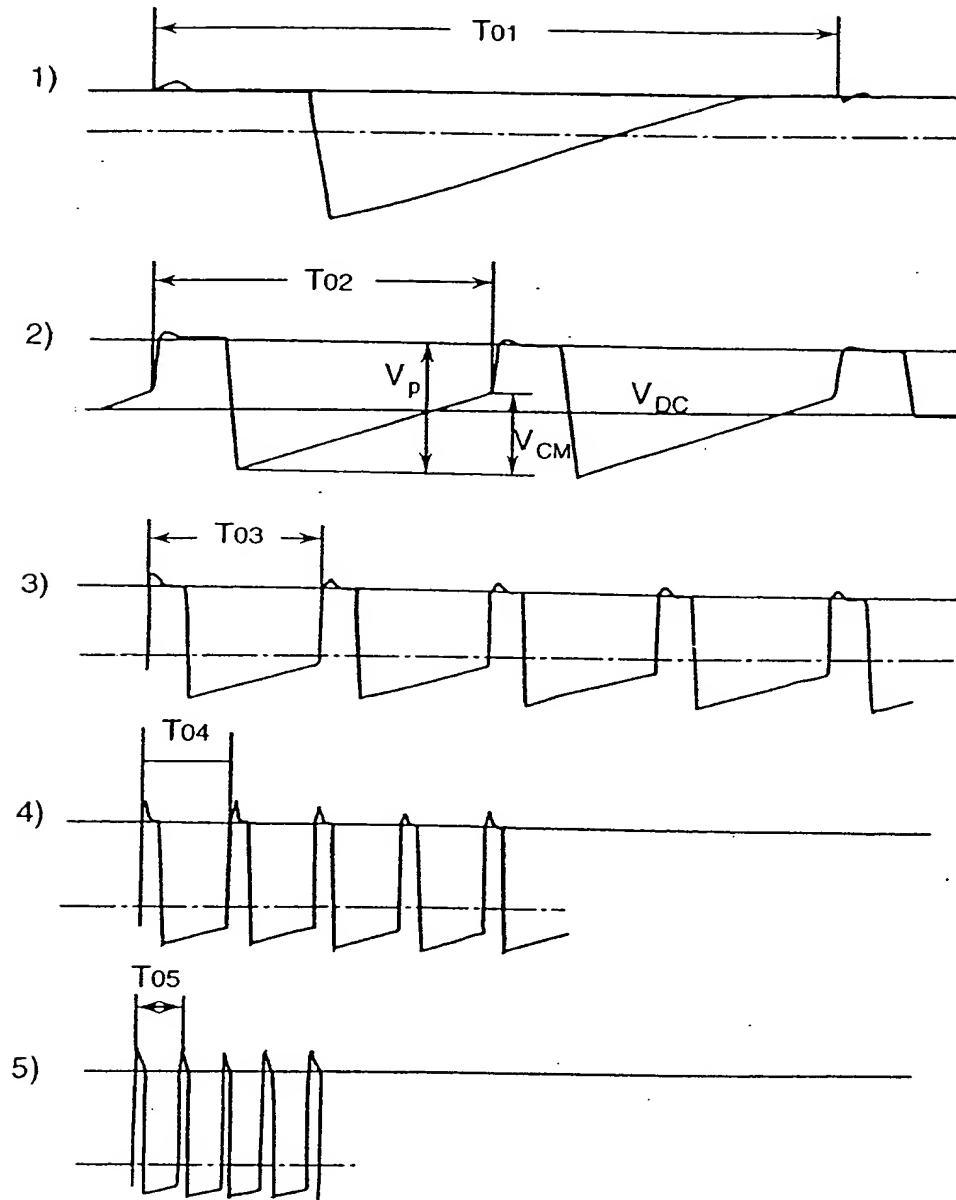
$i_i$  : ION CURRENT DENSITY

$\epsilon_\gamma$  : SPECIFIC DIELECTRIC CONSTANT OF  
ELECTROSTATIC ATTRACTING FILM

$d$  : THICKNESS OF ELECTROSTATIC  
ATTRACTING FILM

$K$  : ELECTRODE COVERING RATIO OF  
ELECTROSTATIC ATTRACTING FILM

FIG. 8



$$T_{01} : T_{02} : T_{03} : T_{04} : T_{05} = 16 : 8 : 4 : 2 : 1$$

FIG. 9

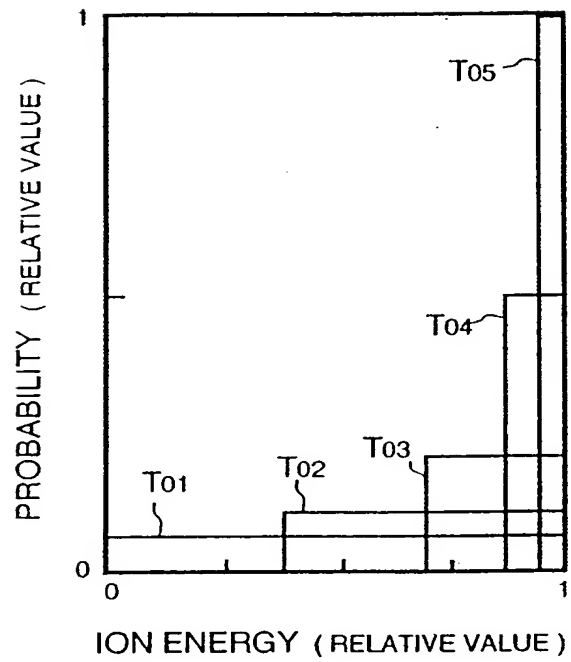




FIG. 10

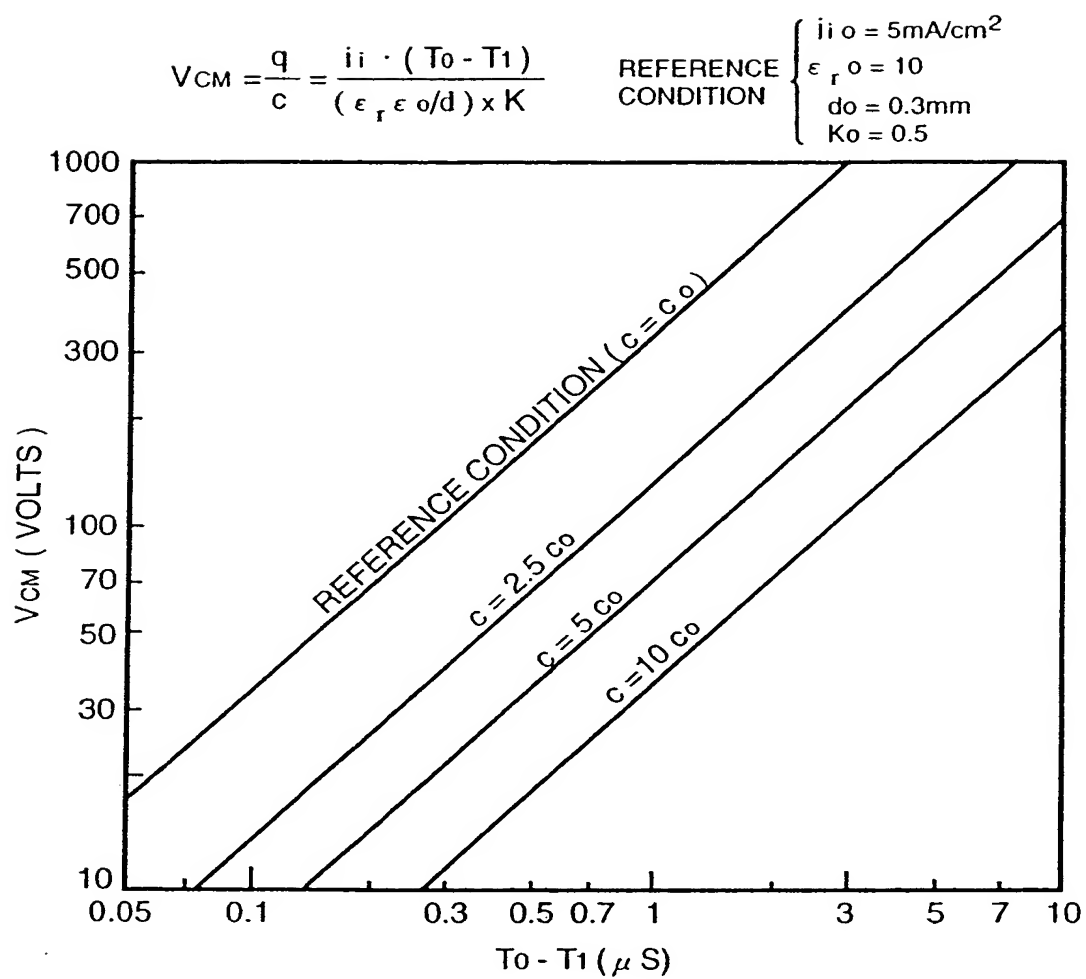


FIG. 11

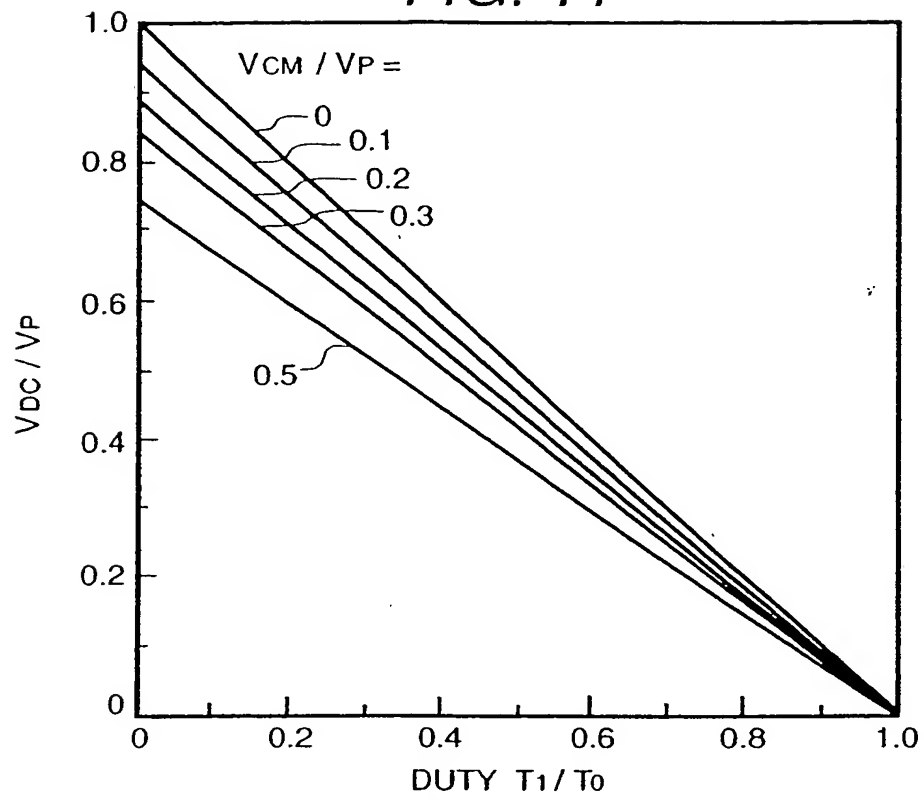


FIG. 12

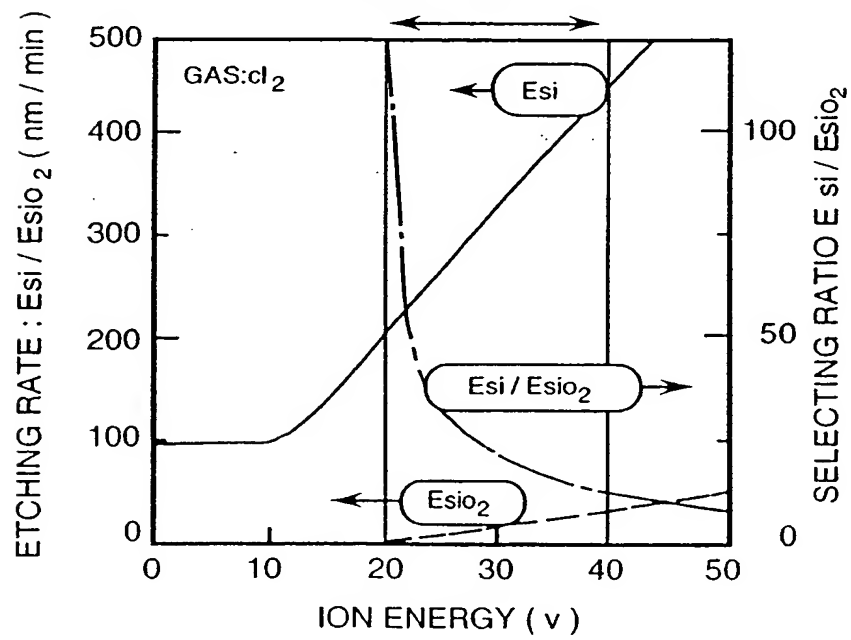


FIG. 13

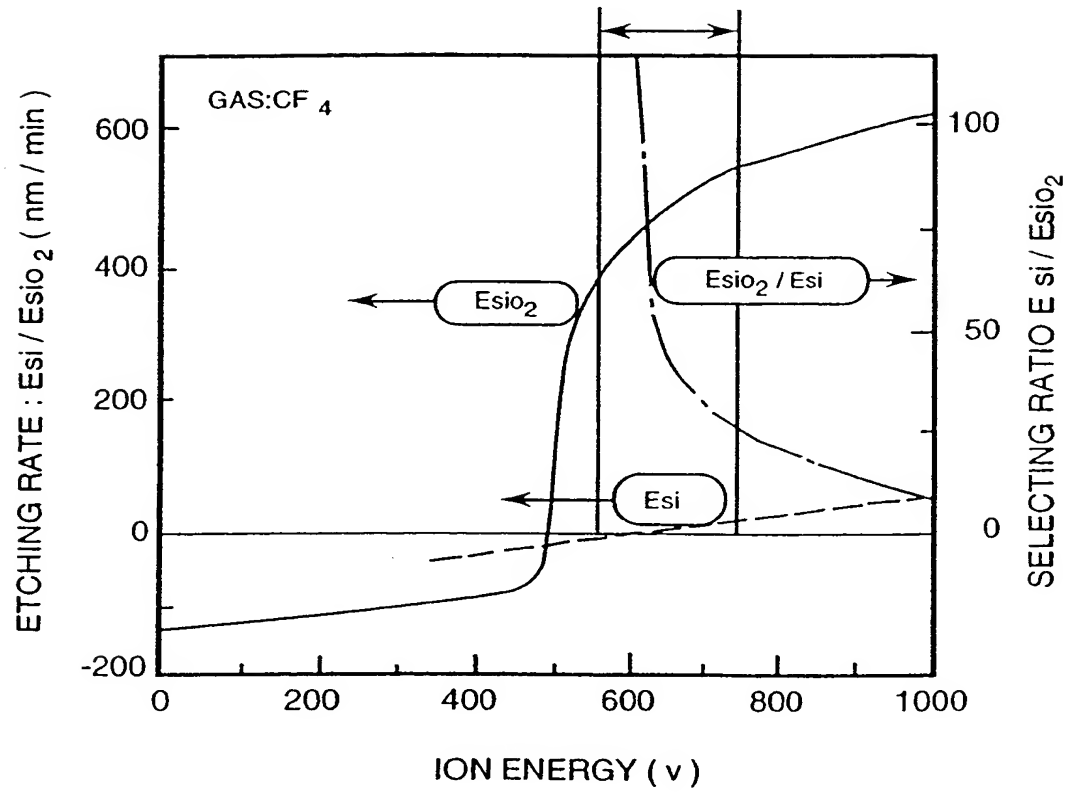


FIG. 14

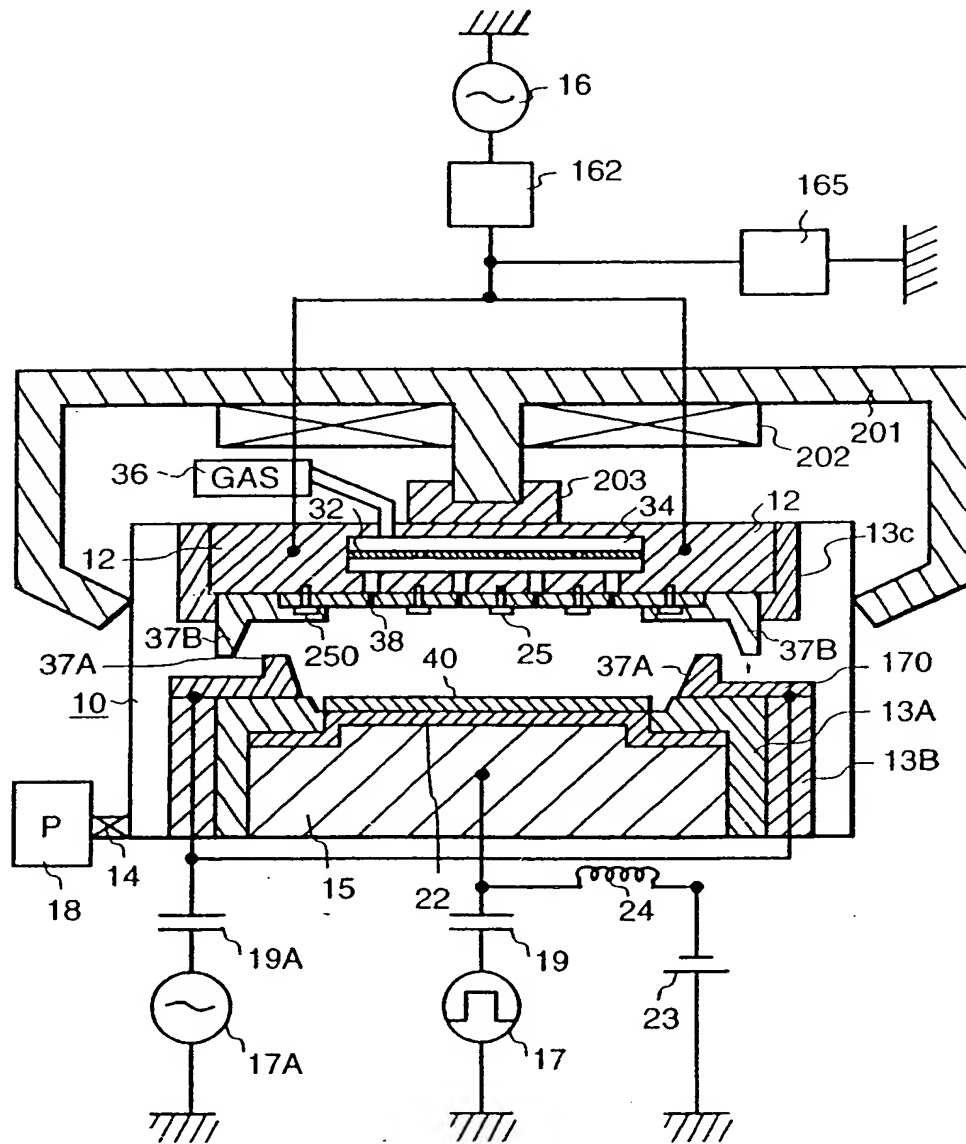


FIG. 15

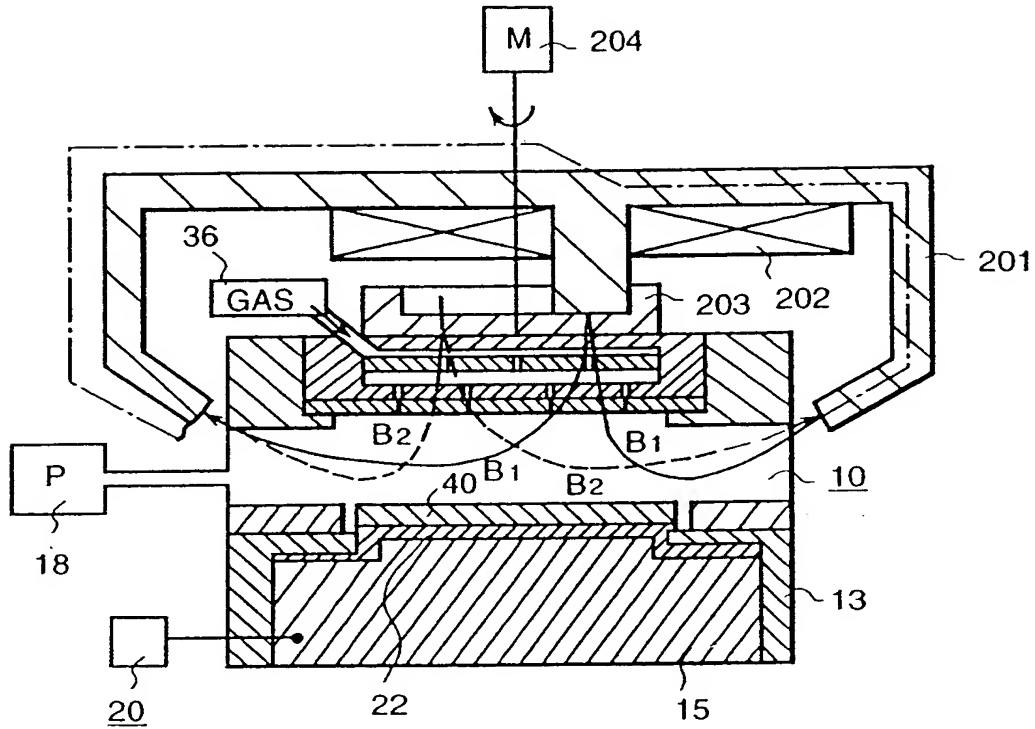


FIG. 16

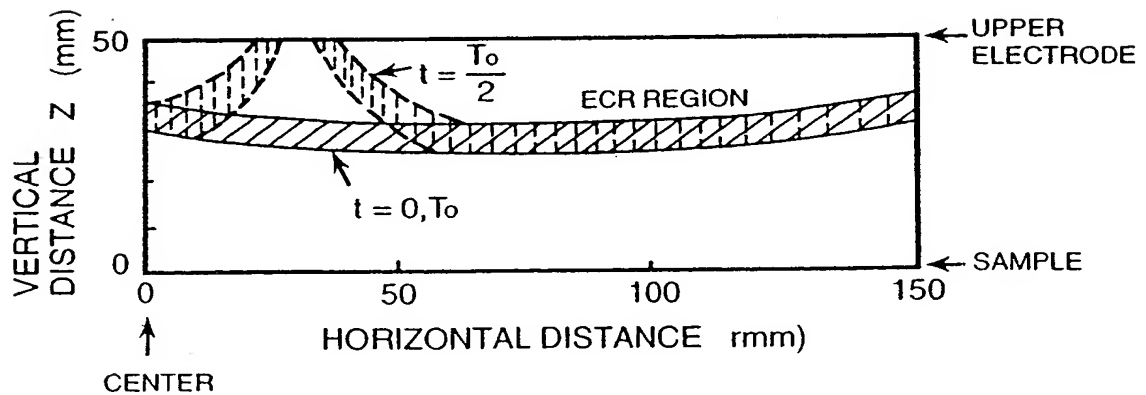


FIG. 17

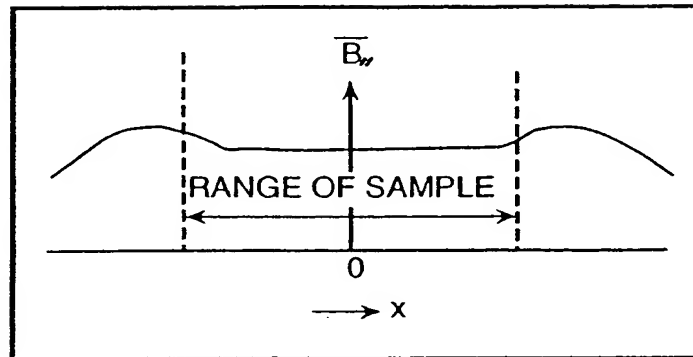


FIG. 18

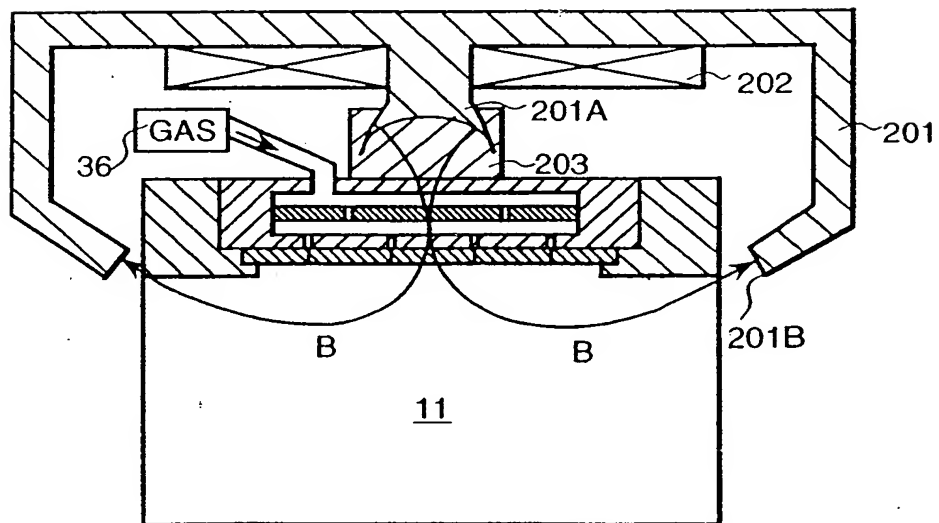


FIG. 19

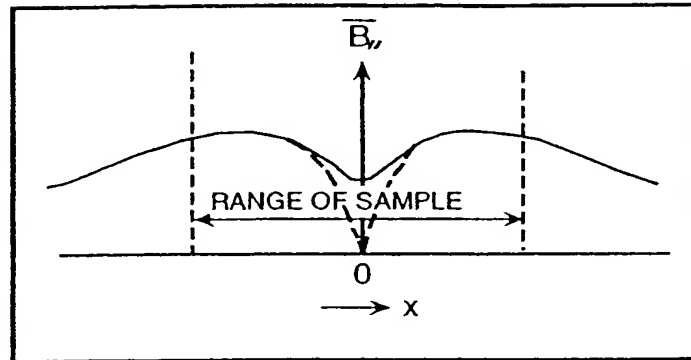


FIG. 20

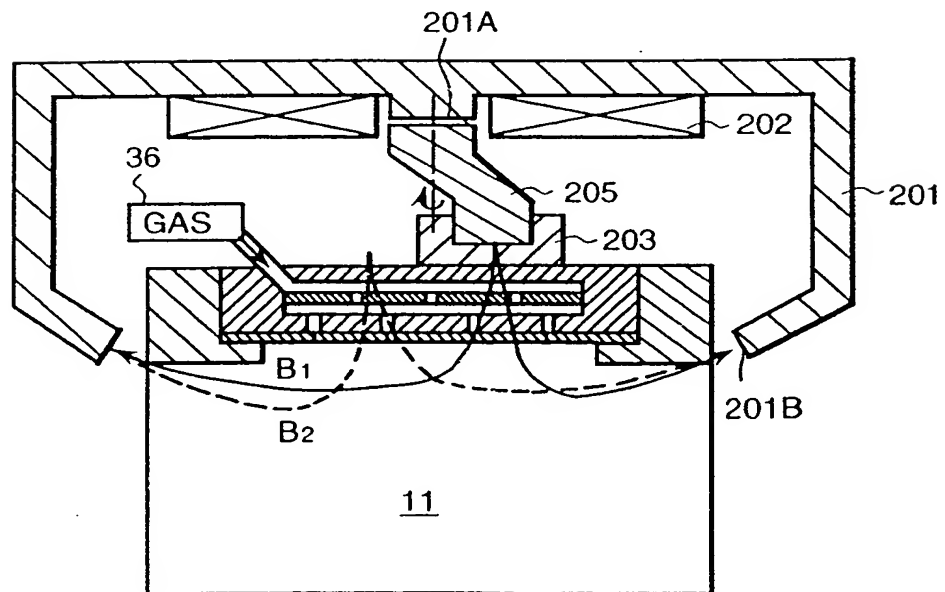


FIG. 21

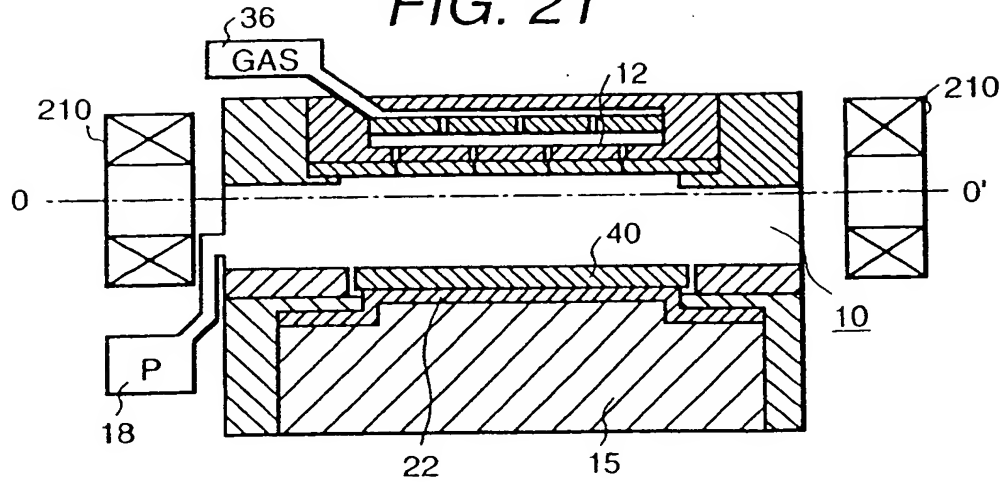


FIG. 22

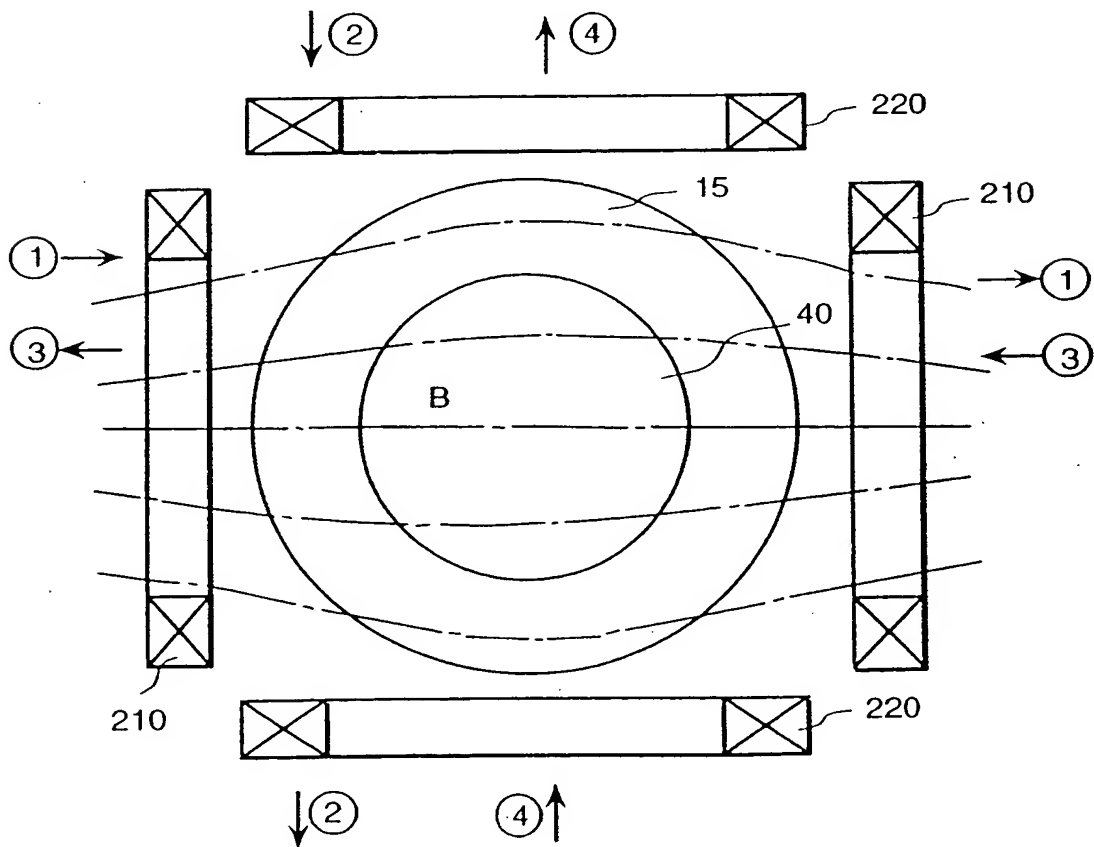




FIG. 23

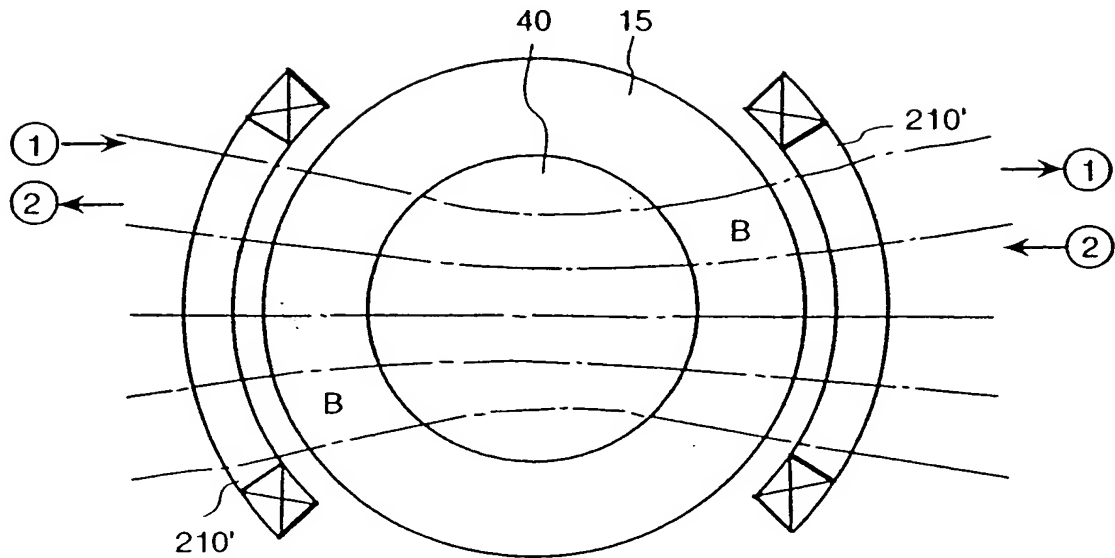


FIG. 24

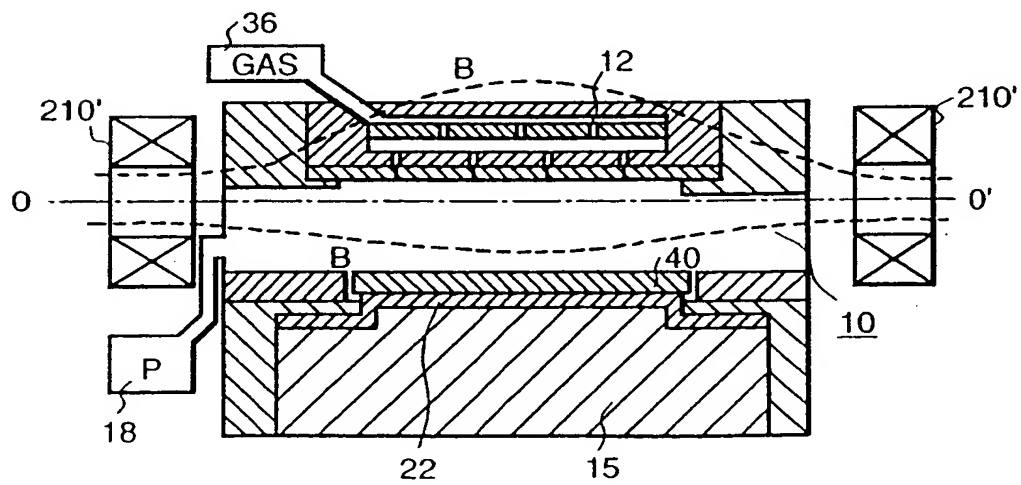


FIG. 25

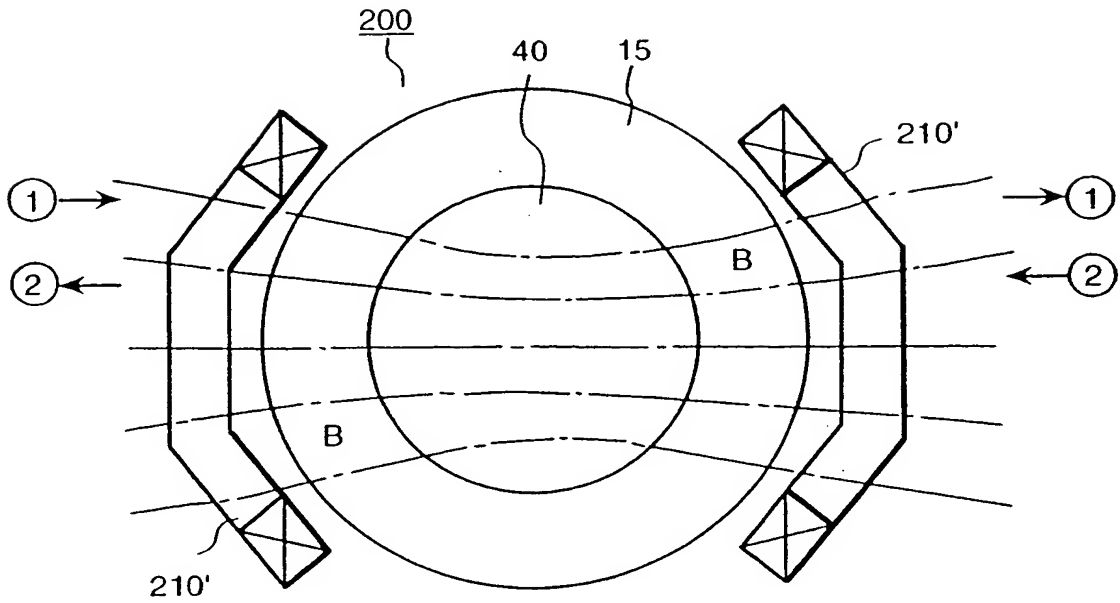


FIG. 26

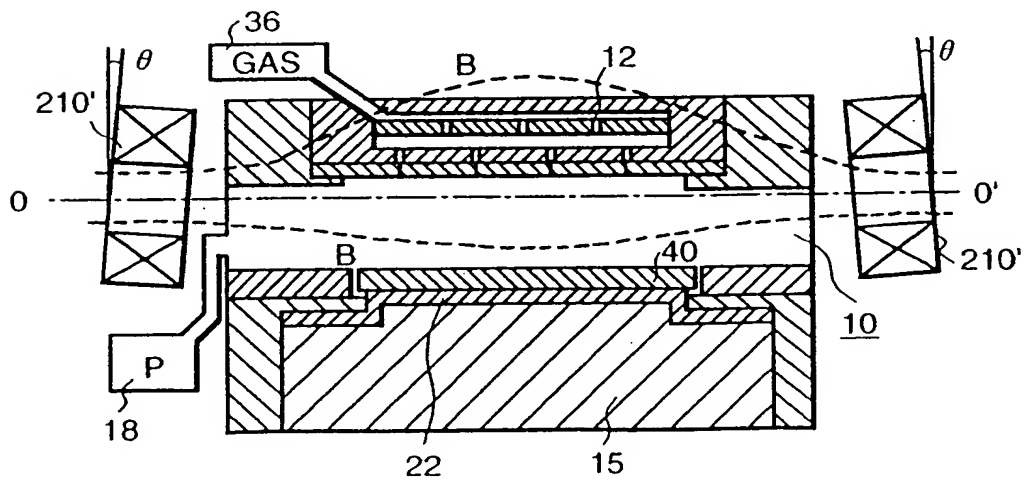




FIG. 28

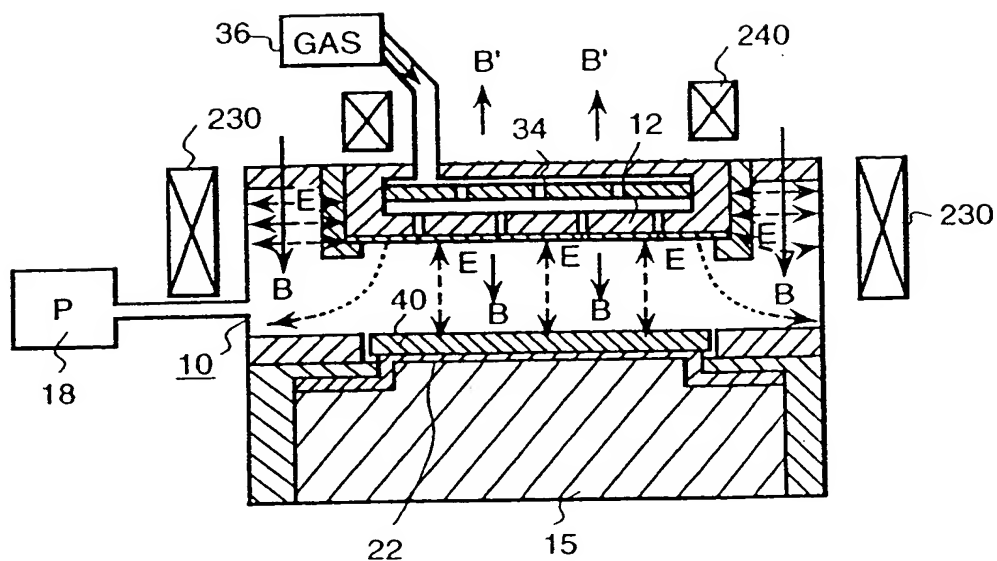


FIG. 29

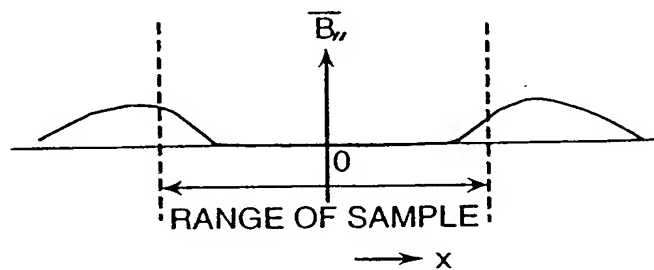


FIG. 30

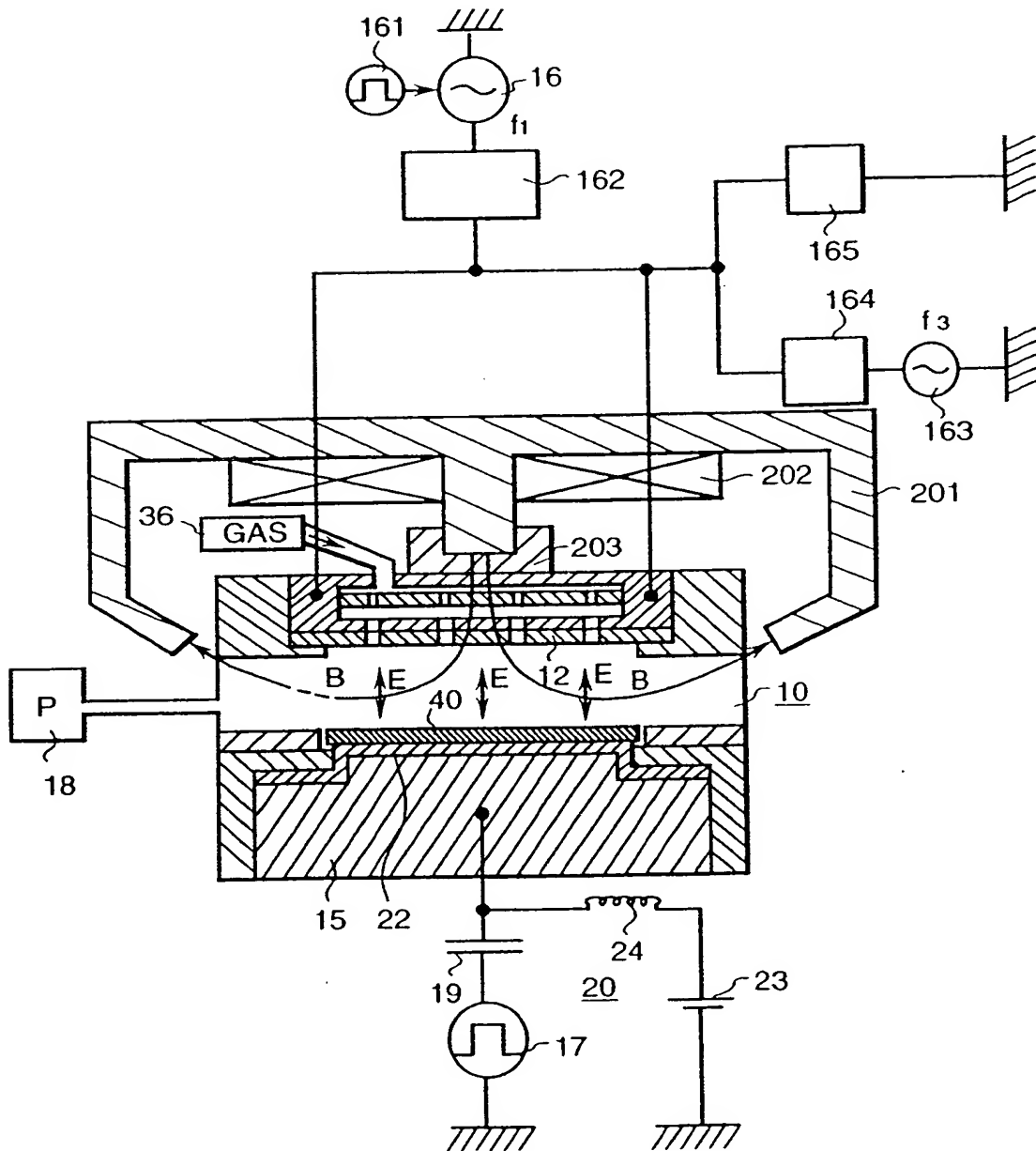


FIG. 31

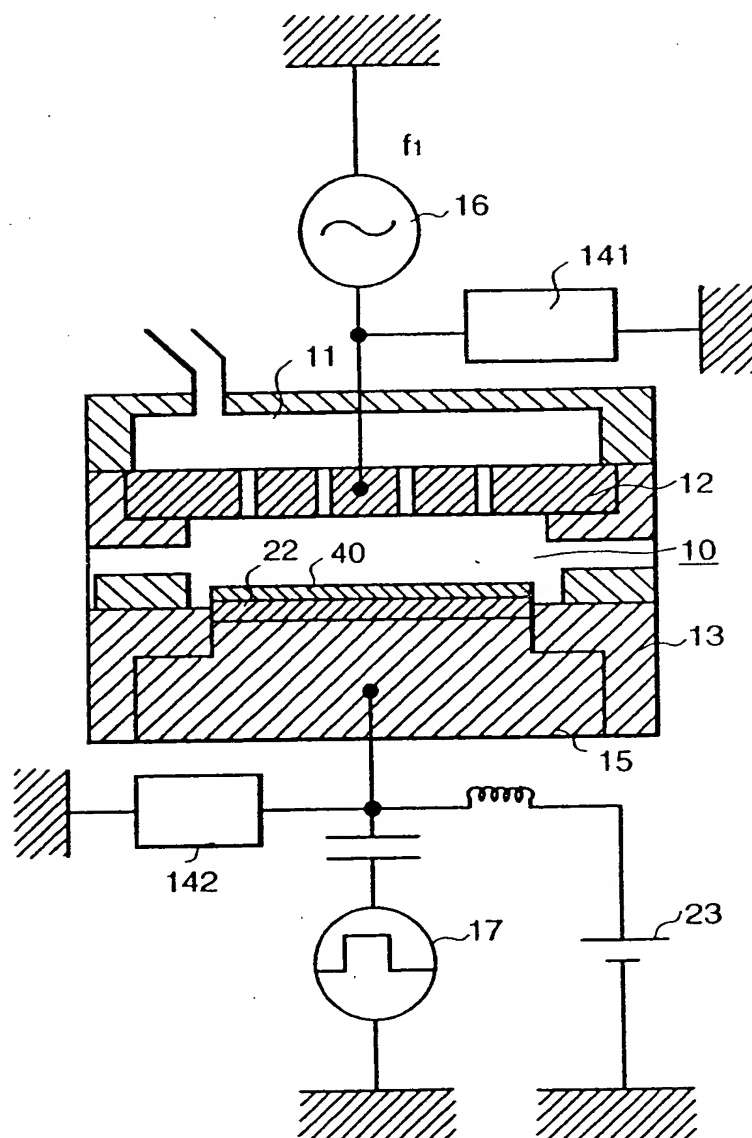
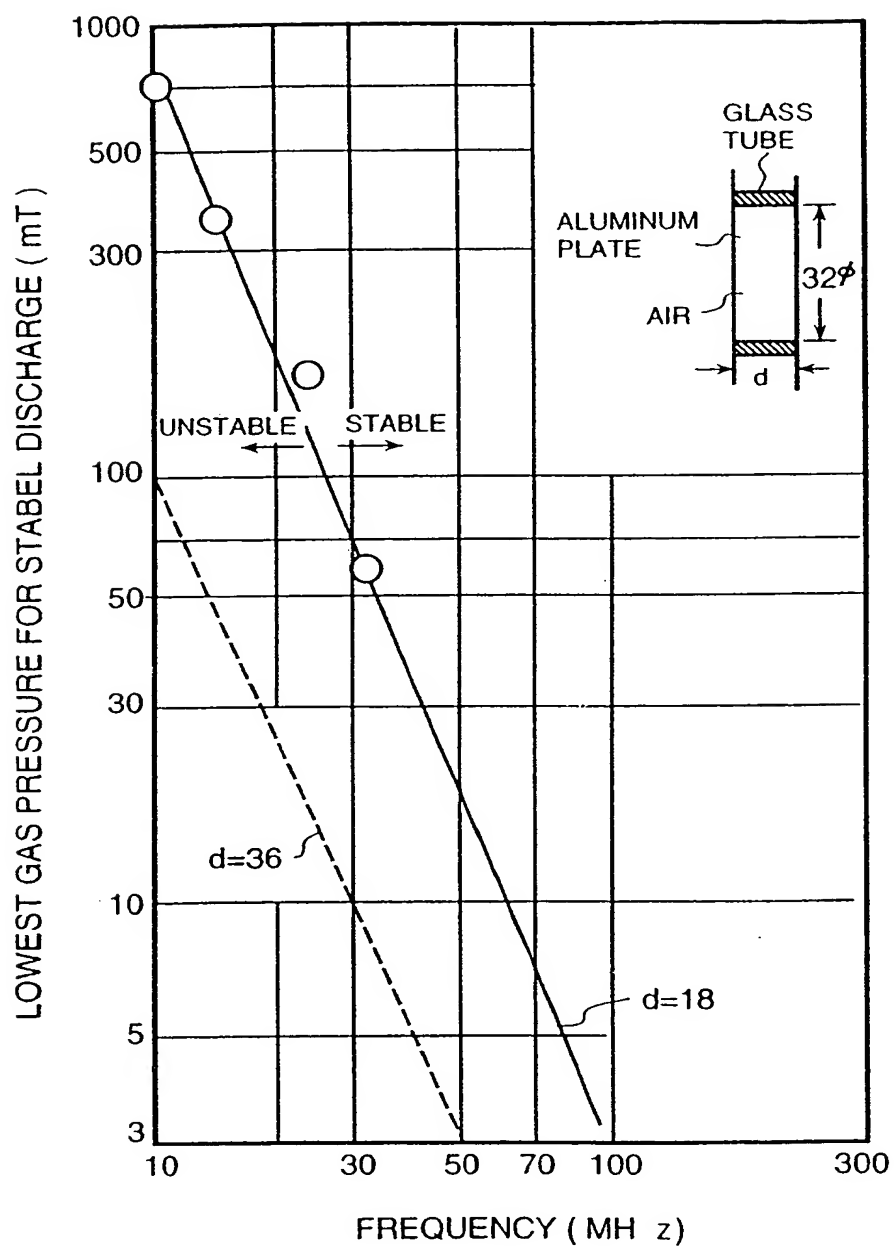


FIG. 32



FREQUENCY-LOWEST GAS PRESSURE FOR  
STABLE DISCHARGE CHARACTERISTIC

FIG. 33

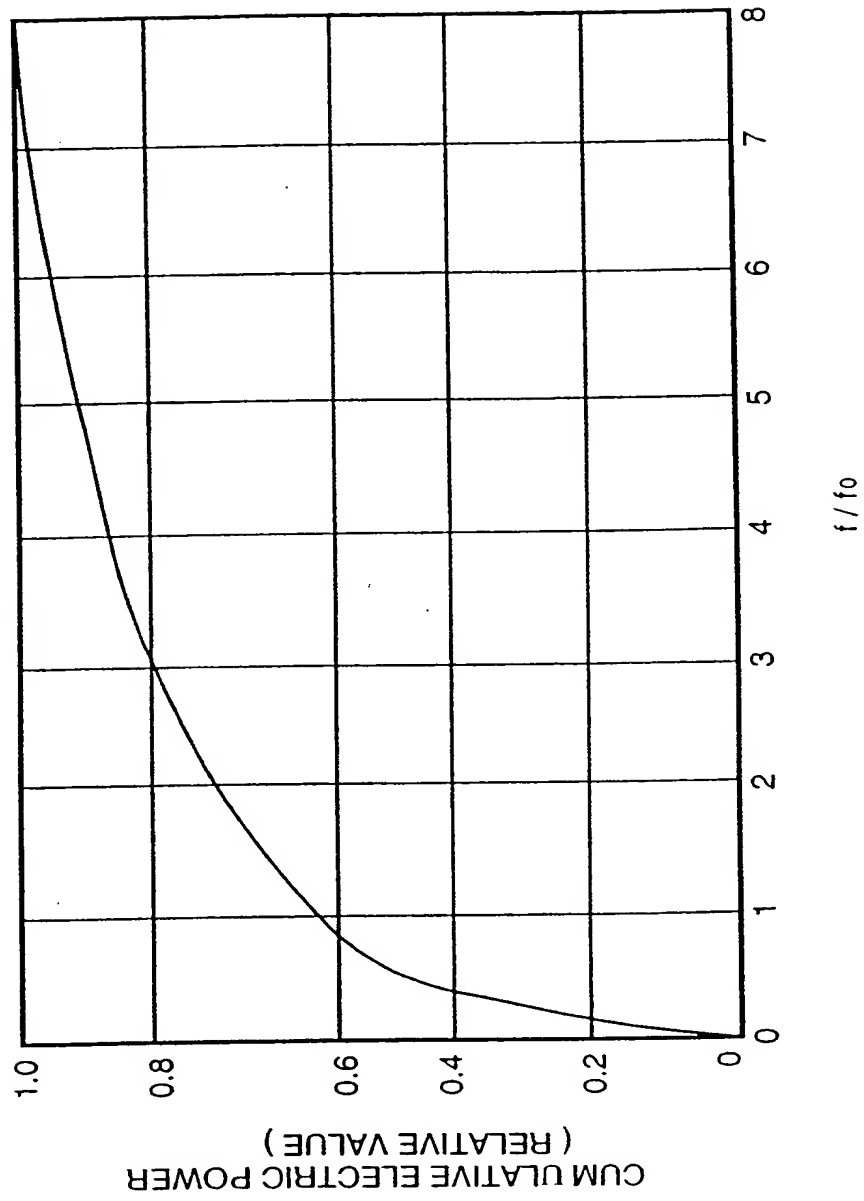




FIG. 34

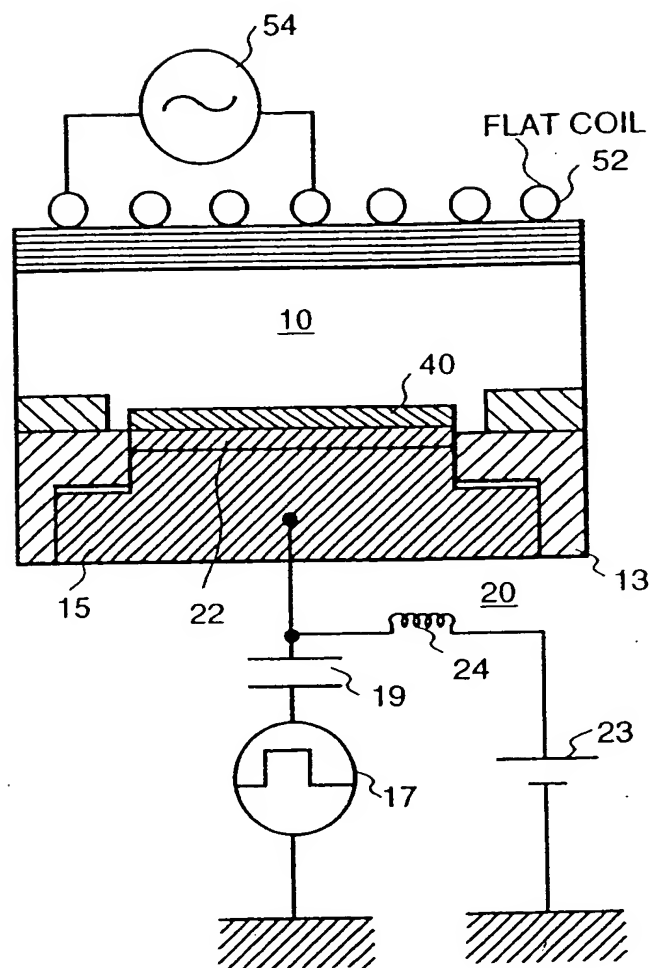


FIG. 35

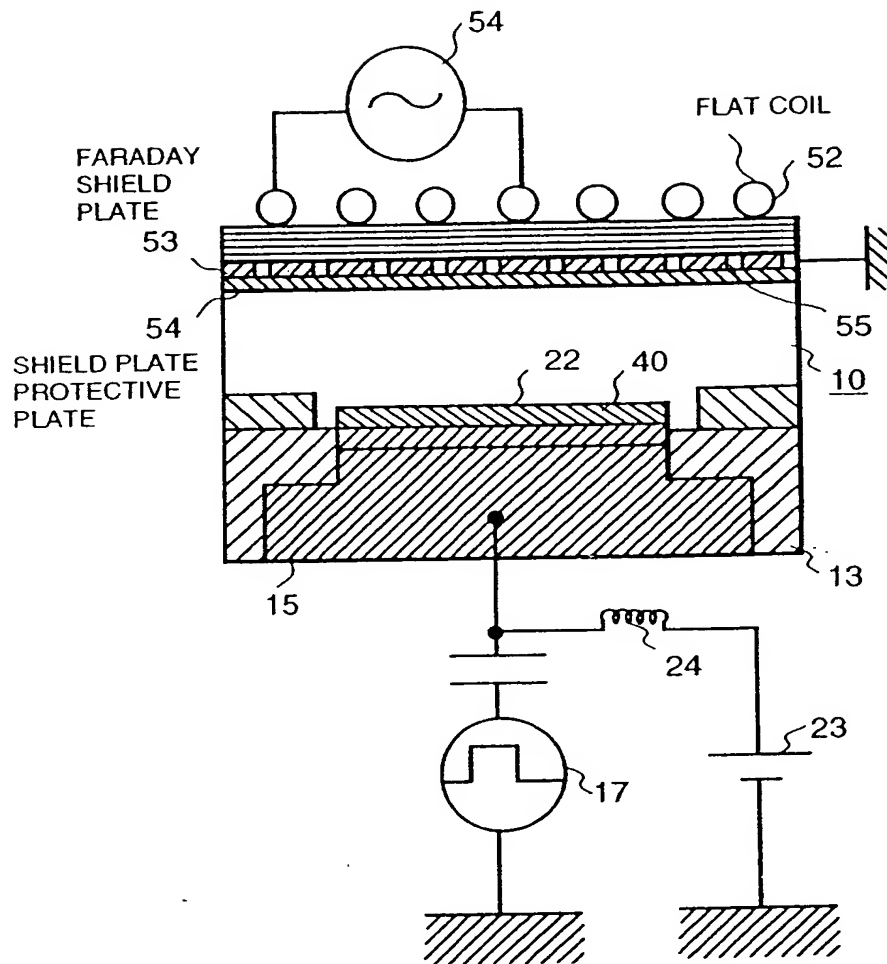


FIG. 36

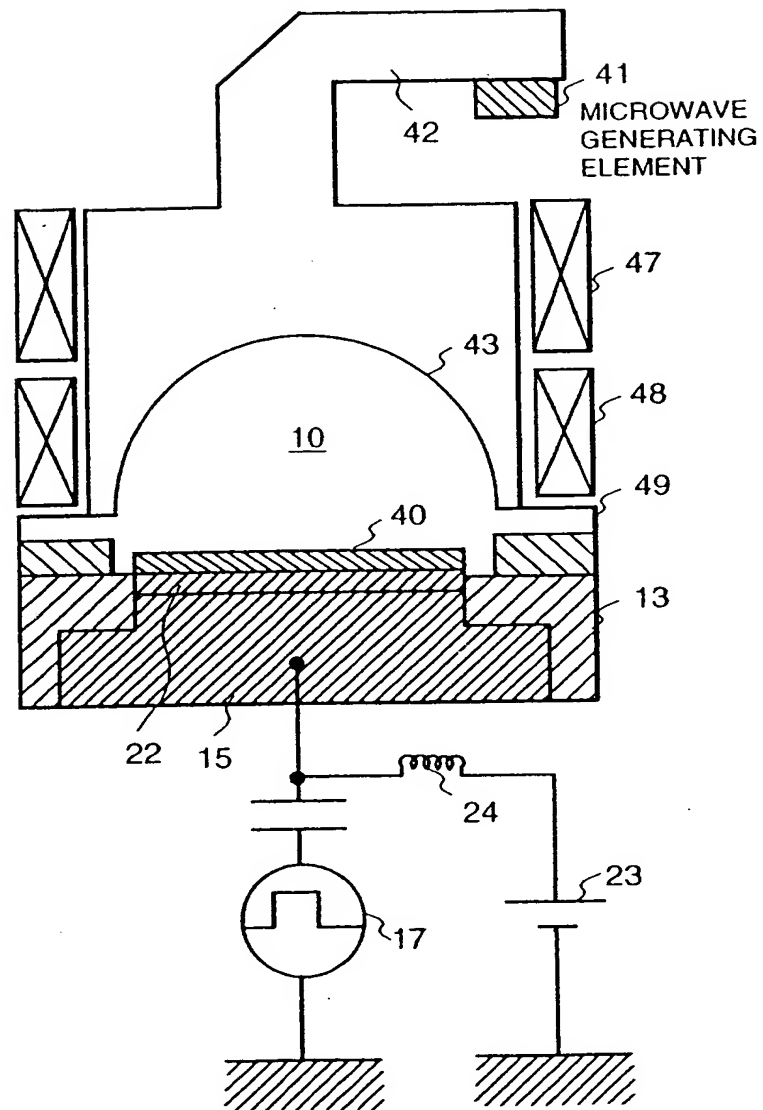


FIG. 37

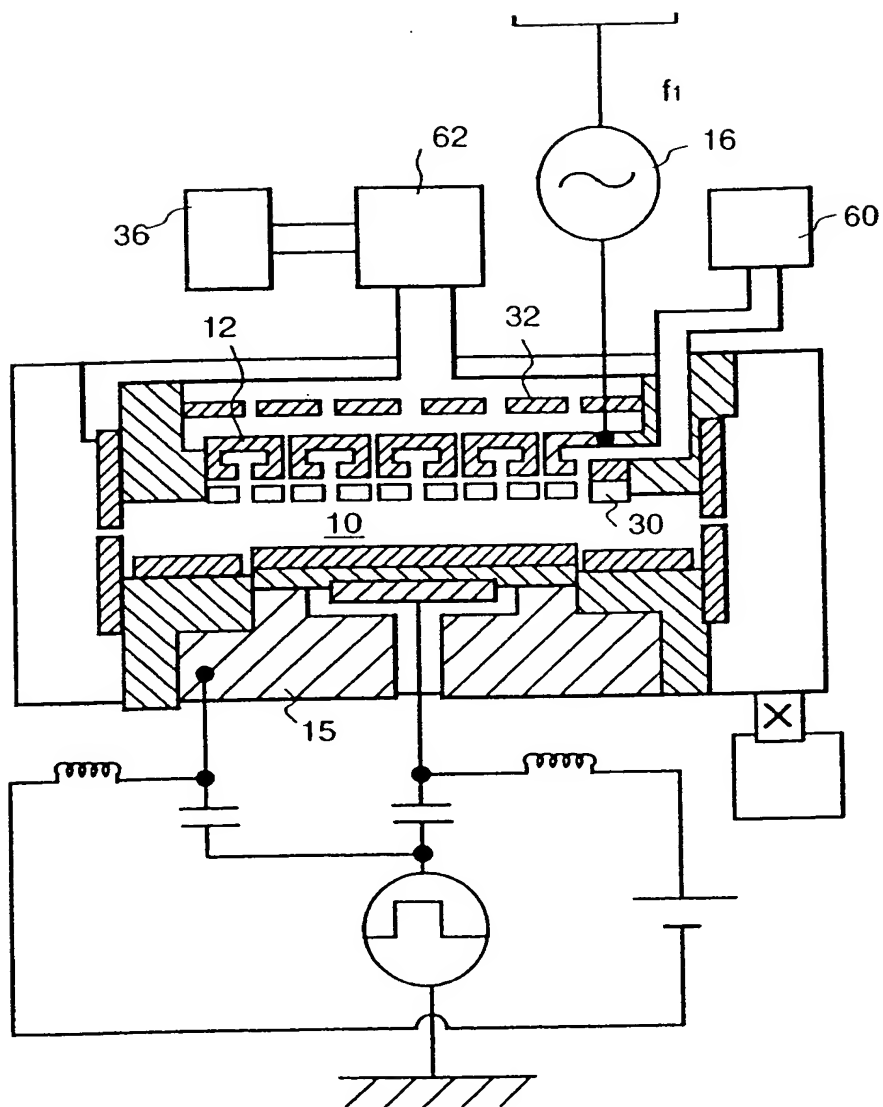


FIG. 38

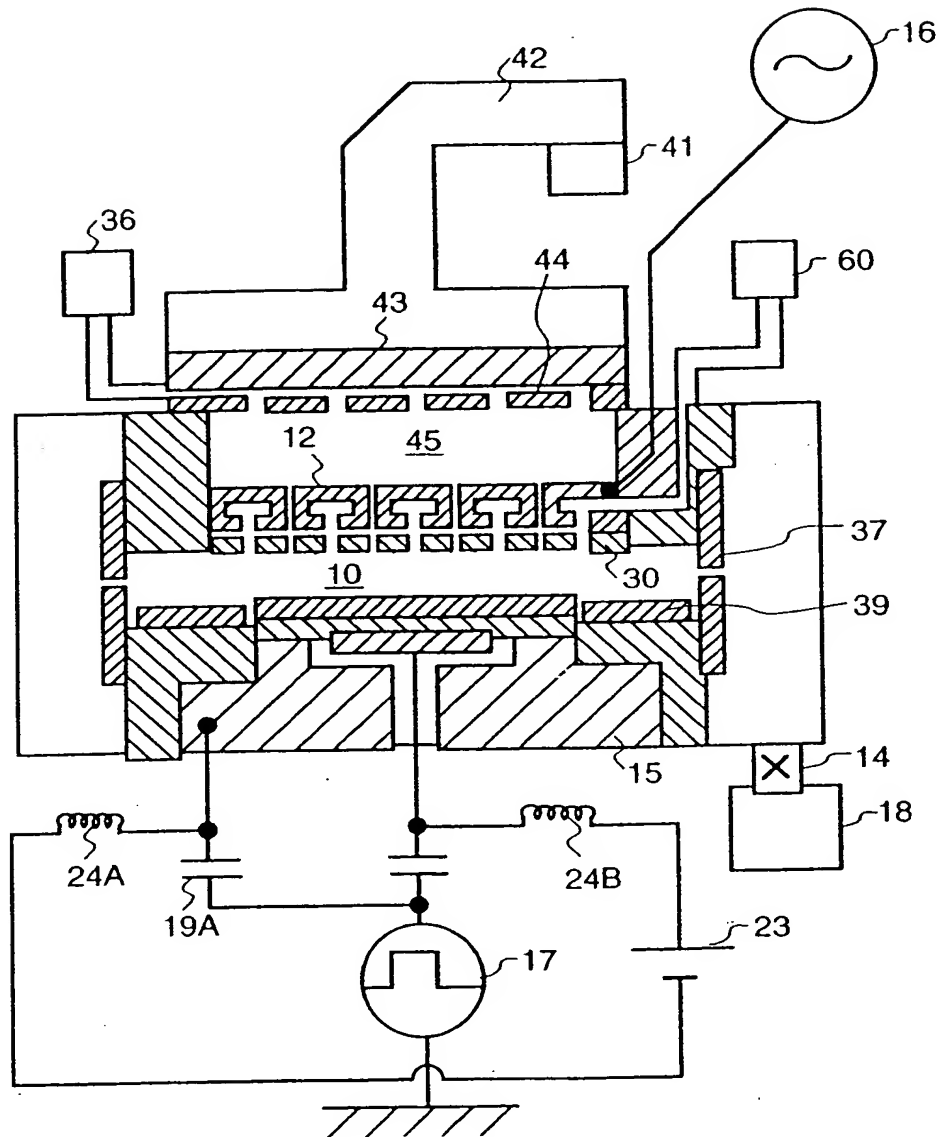


FIG. 39

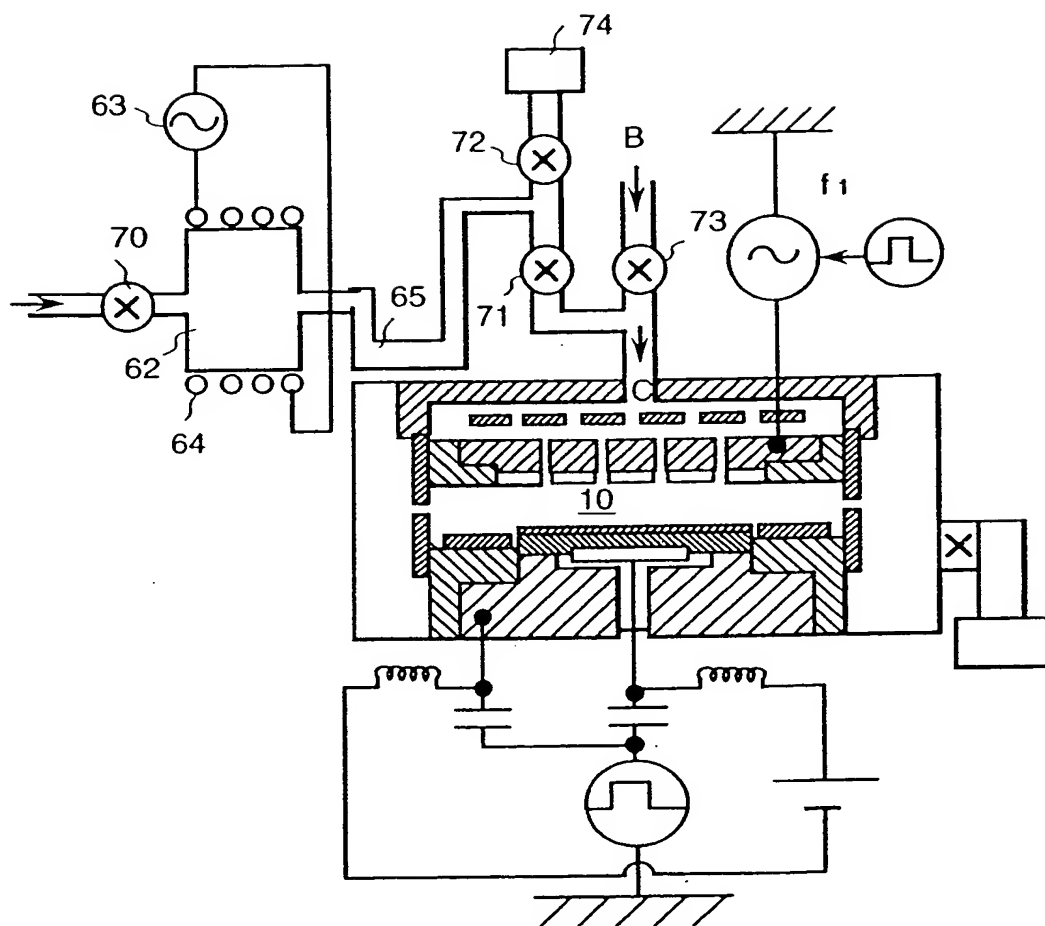


FIG. 40

